



PCIM 议题 EPC

- 为何采用氮化镓器件 (GaN) ?
- 对各种不同拓扑进行评估
- 无线电源应用的品质因数
- 对采用不同器件进行比较
- 实验性验证结果
- 总结

PCIM 无线电源传送应用为何采用氮化镓场效应晶体管 (eGaN FET) EPC

- 具低 C_{ISS} 及 C_{OSS}
- 在相同电压额定值具低 $R_{DS(on)}$
- 纤薄型
- 可选的栅极驱动器:

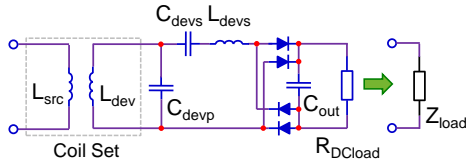


- LM5113
- LM5114
- UCC27611



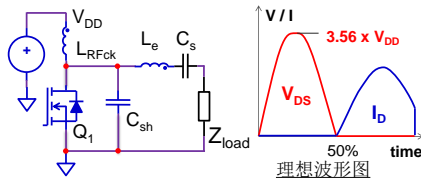
PCIM **简化线圈组合表述** **EPC**
EFFICIENT POWER CO-CONVERSION

为易于比较不同拓扑而简化了的线圈组合表述



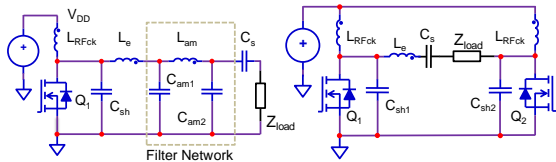
PCIM **Single Ended E类放大器** **EPC**
EFFICIENT POWER CO-CONVERSION


- 开关电压额定值 $\geq 3.56 \cdot V_{DD}$ 供电 (V_{DD})
- C_{OSS} 被匹配網路吸收
- 易受负载变化影响 - 高场效应晶体管损耗
- 线圈电压 $\approx 0.707 \cdot V_{DD} [V_{RMS}]$.




PCIM **E类放大器拓扑的变化** **EPC**
EFFICIENT POWER CO-CONVERSION

- 给不同负载的匹配阻抗滤波器
- 差别模式:
 - 增加输出功率
 - 降低了电压谐波
 - 线圈电压 $\approx 1.414 \cdot V_{DD} [V_{RMS}]$.

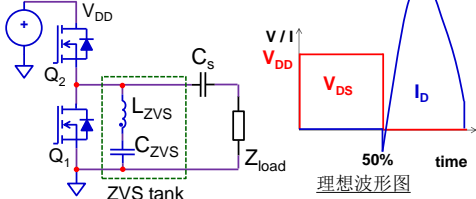




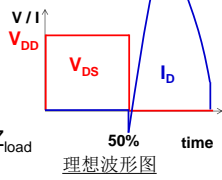
ZVS D类放大器



- 开关电压额定值 = 供电 (V_{DD})
- ZVS 谐振电压经由 C_{OSS} 过渡
- ZVS 谐振电路没有负载电流
- 线圈电压 = $\frac{1}{2} \cdot V_{DD}$ [V_{RMS}].




理想波形图




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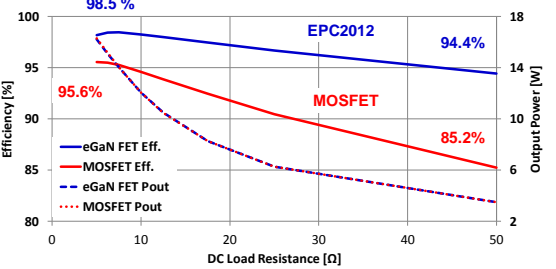




分析及比较E类放大器




最高功率器件损耗 = 279 mW
不需要散热器




DC Load Resistance [Ω]	eGaN FET Eff. [%]	MOSFET Eff. [%]	eGaN FET Pout [W]	MOSFET Pout [W]
10	98.5%	95.6%	~14	~10
50	94.4%	85.2%	~2	~1

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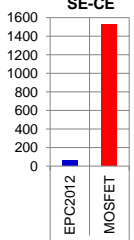




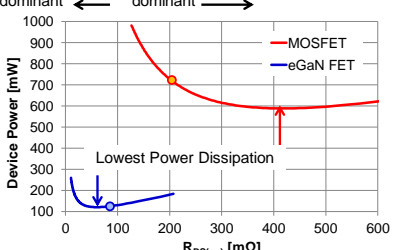
在E类放大器的器件比较



FoM_{WPT} [nC·mΩ]



Gate Power dominant ← → Conduction Loss dominant

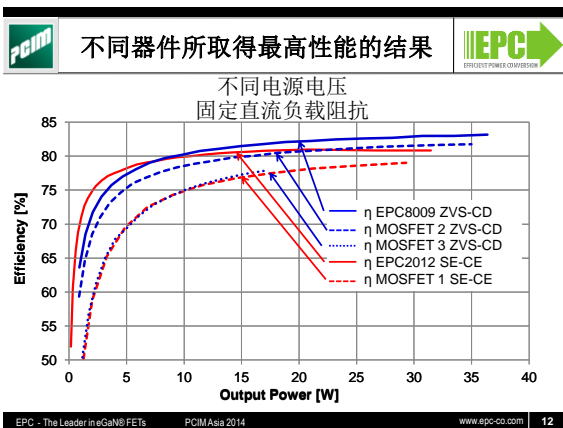
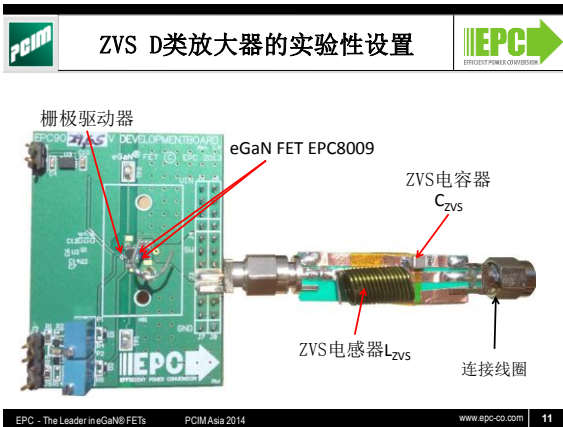
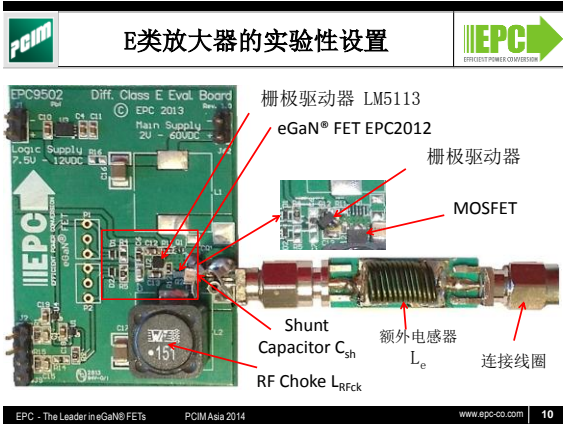


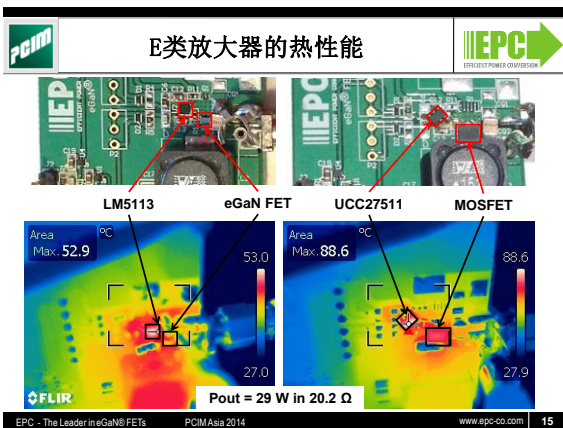
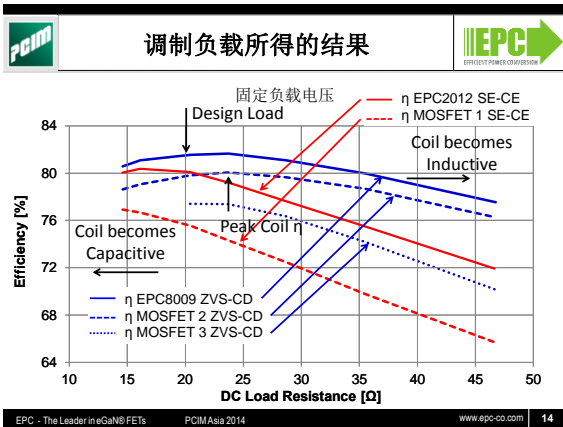
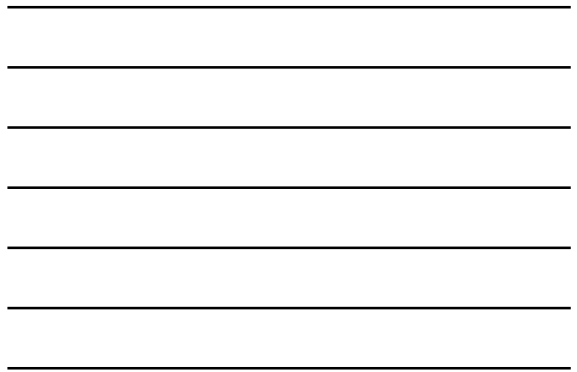
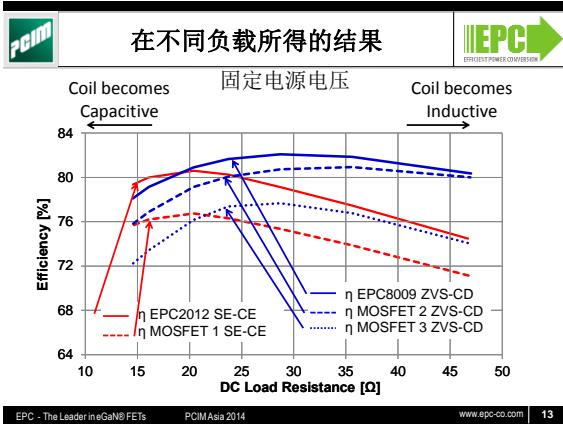
Lowest Power Dissipation

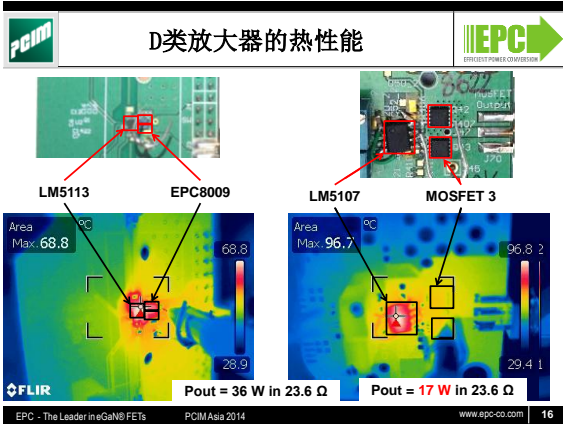
$$FOM_{WPT} = R_{DS(on)} \cdot (Q_G - Q_{GD})$$

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总结

氮化镓场效应晶体管 (eGaN® FET) 在电源传送应用为颠覆性创新器件:

- 推动无线电源传送应用的发展
- 与MOSFET器件相比具更高效率
- 可在6.78 MHz 及13.56 MHz频率工作
- 纤薄型器件
- 易于使用
- 驱动全新拓扑如ZVS D类放大器的出现
- 将进一步普及化—如更多可选栅极驱动器及更多产品使用氮化镓场效应晶体管
